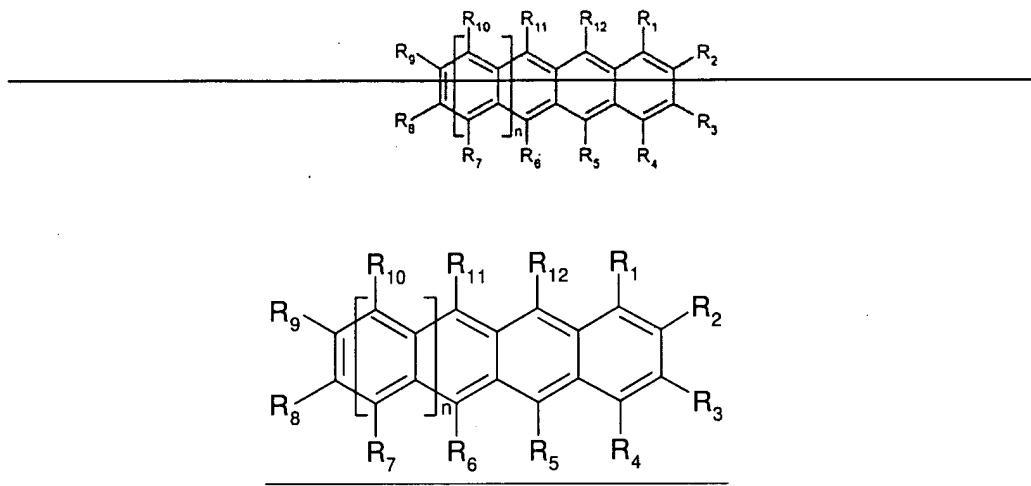


This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) An organic semiconducting layer formulation, comprising an organic binder which has a permittivity, ϵ , at 1,000 Hz of 3.3 or less; and a polyacene compound of Formula A:



Formula A

wherein:

each of R₁, R₂, R₃, R₄, R₅, R₆, R₇, R₈, R₉, R₁₀, R₁₁ and R₁₂, which may be the same or different, independently represents hydrogen; an optionally substituted C₁-C₄₀ carbyl or hydrocarbyl group; an optionally substituted C₁-C₄₀ alkoxy group; an optionally substituted C₆-C₄₀ aryloxy group; an optionally substituted C₇-C₄₀ alkylaryloxy group; an optionally substituted C₂-C₄₀ alkoxy carbonyl group; an optionally substituted C₇-C₄₀ aryloxycarbonyl group; a cyano group (-CN); a carbamoyl group (-C(=O)NH₂); a haloformyl group (-C(=O)-X, wherein X represents a halogen atom); a formyl group (-C(=O)-H); an isocyano group; an isocyanate group; a thiocyanate group or a thioisocyanate group; an optionally substituted amino group; a hydroxy group; a nitro group; a CF₃ group; a halogen group; or an optionally substituted silyl group;

wherein independently each pair of R₂ and R₃ and/or R₈ and R₉, may be cross-bridged to form

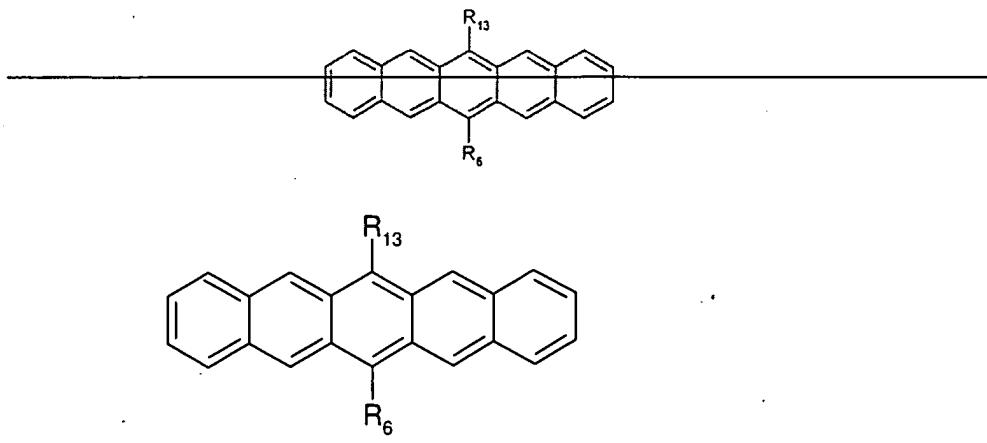
a C₄-C₄₀ saturated or unsaturated ring, which saturated or unsaturated ring may be intervened by an oxygen atom, a sulphur atom or a group shown by formula -N(R_a)- (wherein R_a is a hydrogen atom or an optionally substituted hydrocarbon group), or may optionally be substituted;

wherein one or more of the carbon atoms of the polyacene skeleton may optionally be substituted by a N, P, As, O, S, Se or Te atom; and wherein independently any two or more of the substituents R₁-R₁₂ which are located on adjacent ring positions of the polyacene may, together, optionally constitute a further C₄-C₄₀ saturated or unsaturated ring optionally interrupted by O, S or -N(R_a) where R_a is as defined above) or an aromatic ring system, fused to the polyacene;

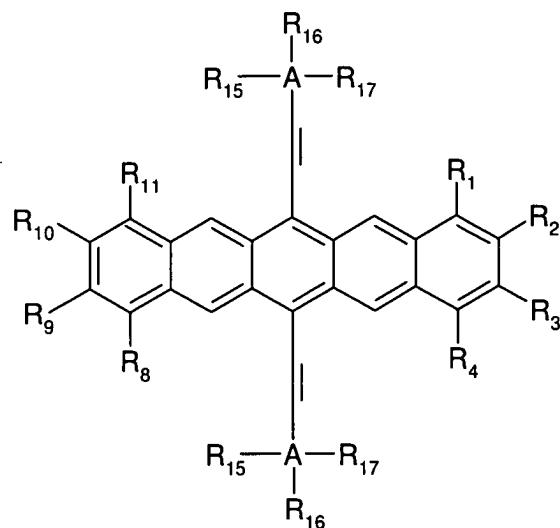
at least one of R₁ to R₁₂ is an optionally substituted C₁-C₄₀ hydrocarbyl group that is a saturated or unsaturated acyclic group, or a saturated or unsaturated cyclic group, and

n is 0, 1, 2, 3 or 4.

2. (Currently Amended) An organic semiconducting layer formulation as claimed in claim 1, wherein the polyacene compound is a compound of formula B 4 or 8 or an isomer thereof



Formula B 4



Formula 8

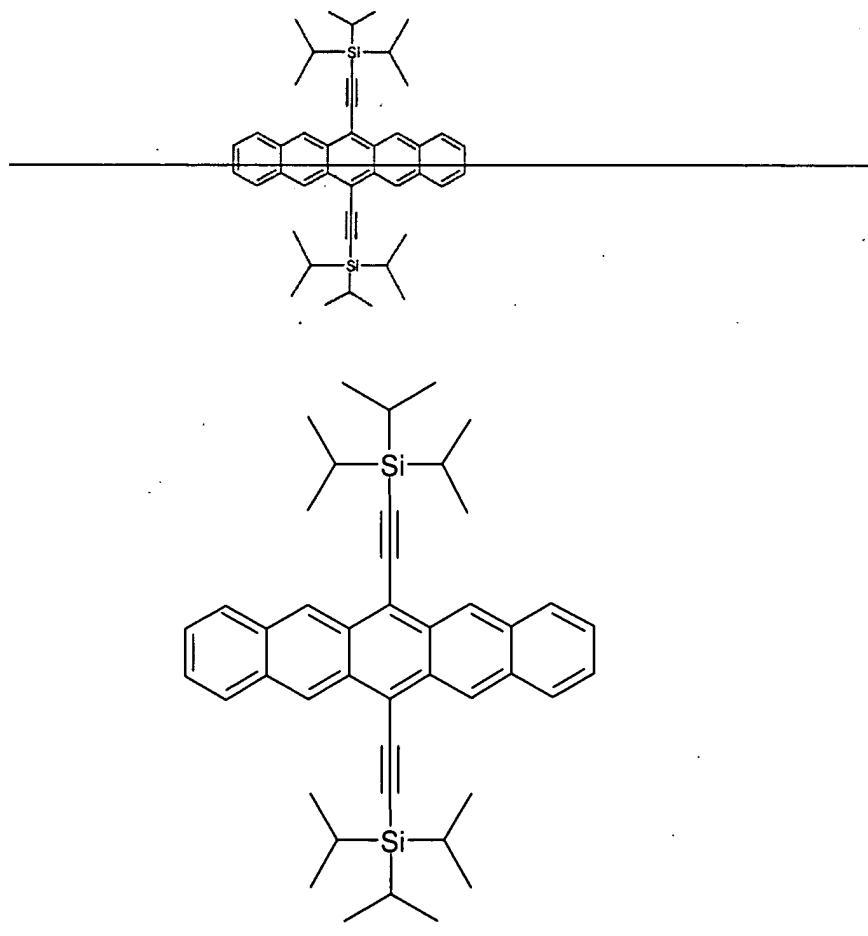
wherein, R₆ and R₁₃ in the compound of formula 1 and R₁, R₂, R₃, R₄, R₈, R₉, R₁₀, R₁₁, R₁₅, R₁₆, and R₁₇, in the compound of formula 8 are each independently the same or different and each independently represents: H; an optionally substituted C₁-C₄₀ carbyl or hydrocarbyl group; an optionally substituted C₁-C₄₀ alkoxy group; an optionally substituted C₆-C₄₀ aryloxy group; an optionally substituted C₇-C₄₀ alkylaryloxy group; an optionally substituted C₂-C₄₀ alkoxy carbonyl group; an optionally substituted C₇-C₄₀ aryloxycarbonyl group; a cyano group (-CN); a carbamoyl group (-C(=O)NH₂); a haloformyl group (-C(=O)-X, wherein X represents a halogen atom); a formyl group (-C(=O)-H); an isocyano group; an isocyanate group; a thiocyanate group or a thioisocyanate group; an optionally substituted amino group; a hydroxy group; a nitro group; a CF₃ group; a halogen group; or an optionally substituted silyl group; and wherein independently each pair of R₁ and R₂, R₂ and R₃, R₃ and R₄, R₈ and R₉, R₉ and R₁₀, R₁₀ and R₁₁, R₁₅ and R₁₆ and R₁₆ and R₁₇ may be cross-bridged with each other to form a C₄-C₄₀ saturated or unsaturated ring, which saturated or unsaturated ring may be intervened by an oxygen atom, a sulphur atom or a group shown by formula: -N(R_a)- (wherein R_a is a hydrogen atom or a hydrocarbon group), or may optionally be substituted; and wherein A represents Silicon or Germanium.

3. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 1, wherein n is 0 or 2.

4. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 3, wherein n is 2.

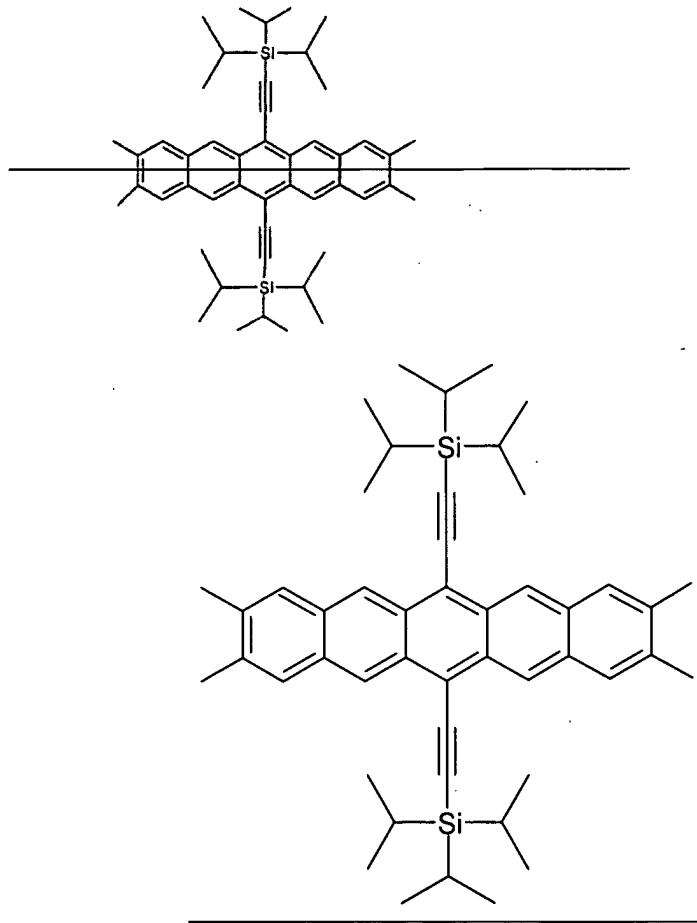
5. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 1, wherein two or more of R₁ to R₁₂ are optionally substituted C₁-C₄₀ hydrocarbyl groups, each of which is a saturated or unsaturated acyclic group, or a saturated or unsaturated cyclic group.

6. (Currently Amended) An organic semiconducting layer formulation as claimed in claim 28, wherein the polyacene compound is 6, 13-bis(triisopropylsilyl)pentacene of Formula 1,



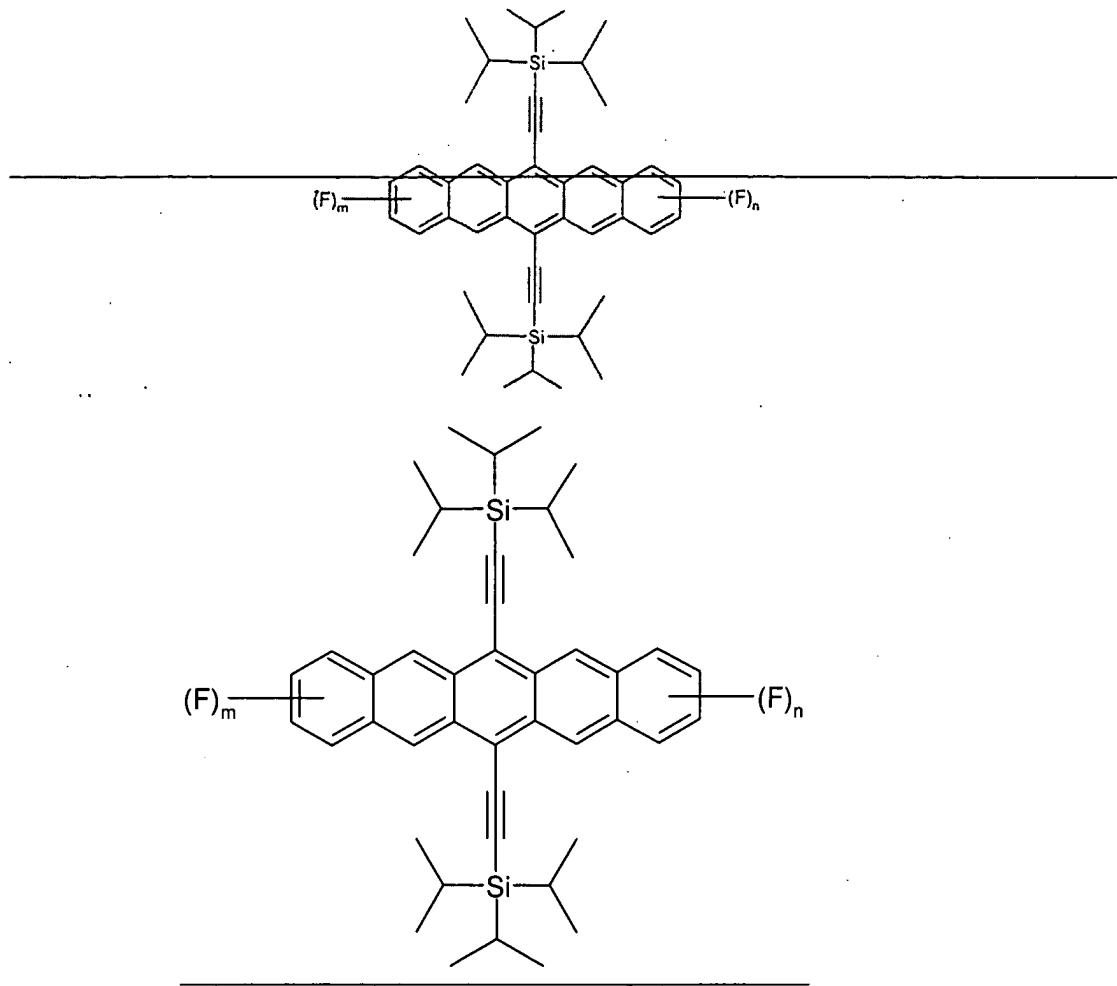
Formula 1.

7. (Currently Amended) An organic semiconducting layer formulation as claimed in claim 28, wherein the polyacene compound is 2,3,9,10-tetramethyl,6,13-bis (triisopropylsilyl)ethynyl)pentacene of Formula 2:



Formula 2.

8. (Currently Amended) An organic semiconducting layer formulation as claimed in claim 28, wherein the polyacene compound is of Formula 3:



Formula 3

wherein n and m are each independently 0,1, 2, 3 or 4.

9. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 1, wherein the organic binder resin has a permittivity at 1,000 Hz of less than 3.0.

10. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 10, wherein the organic binder resin has a permittivity at 1,000 Hz greater than 1.7.

11. (Previously Amended) An organic semiconducting layer formulation

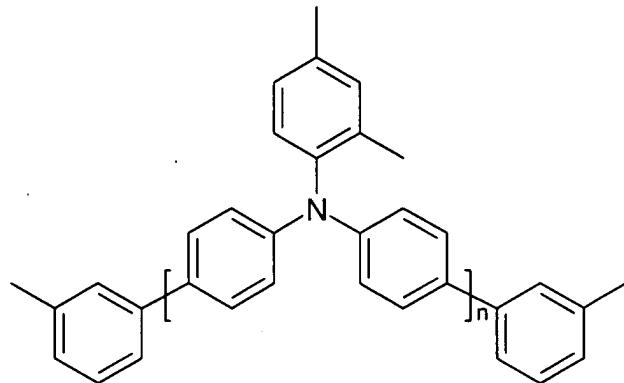
as claimed in claim 1, wherein the organic binder resin is an insulating binder.

12. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 11, wherein the insulating binder is poly(α -methylstyrene), polyvinylcinnamate, poly(4-vinylbiphenyl), poly(4-methylstyrene) or linear olefin and cycloolefin(norbornene)copolymer.

13. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 1, wherein the organic binder resin is a semiconductor binder.

14. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 13, wherein the semiconductor binder comprises a number average molecular weight (M_n) of at least 1500-2000.

15. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 13, wherein the semiconductor binder is poly(9-vinylcarbazole) or a triarylamine compound of the following formula



wherein $n=10.7$.

16. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 1, wherein the formulation further comprises a solvent.

17. (Previously Amended) An organic semiconducting layer formulation as

claimed in claim 16, wherein the solvent is xylene(s), toluene, tetralin or odichlorobenzene.

18. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 1, wherein the ratio of polyacene compound to binder is 20:1 to 1:20 by weight.

19. (Previously Amended) An organic semiconducting layer formulation as claimed in claim 1, which has a solids content of 0.1 to 10% by weight.

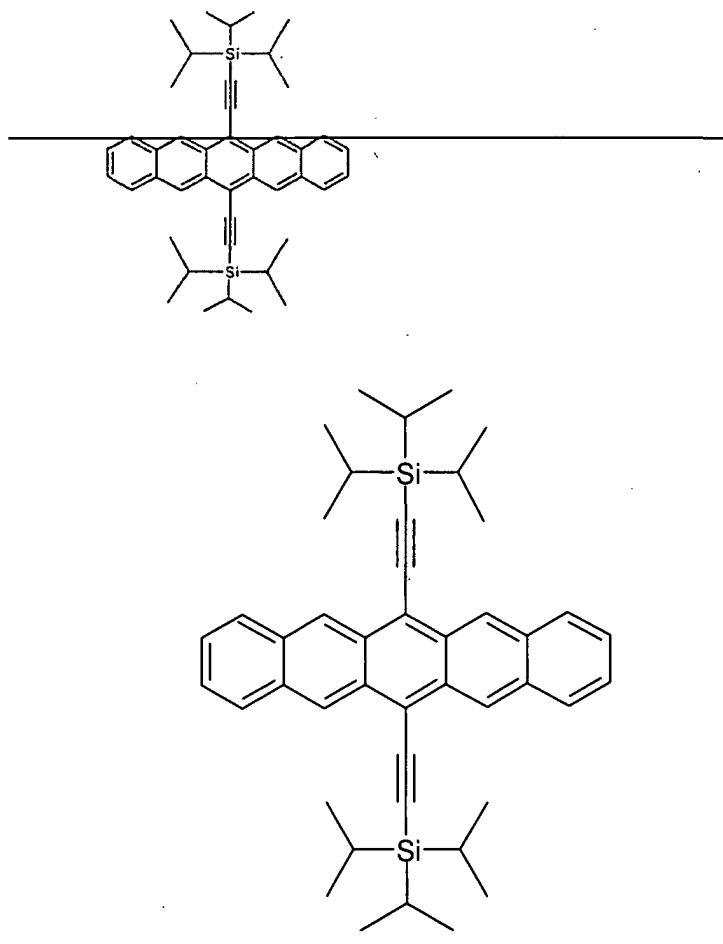
20. (Previously Amended) A process for preparing an organic semiconducting layer formulation as claimed in claim 1, comprising (i) depositing on a substrate a liquid layer of a mixture which comprises the polyacene compound, the organic binder resin or precursor thereof and optionally a solvent, and (ii) forming from the liquid layer a solid layer which is the organic semiconducting layer.

21. (Currently Amended) An In an electronic device, wherein the improvement comprises the presence of comprising an organic semiconducting layer formulation as claimed in claim 1 in said electronic device.

22. (Currently Amended) An electronic device according to claim 21, which comprises a A field effect transistor (FET), organic light emitting diode (OLED), photodetector, chemical detector, photovoltaic cell (PVs), capacitor sensor, logic circuit, display or memory device, comprising an organic semiconducting layer formulation as claimed in claim 1.

23. (Currently Amended) An OFET device, comprising an organic semiconducting layer formulation, wherein the organic semiconducting layer formulation comprises:

a compound of Formula 1;
a binder; and
solvent,

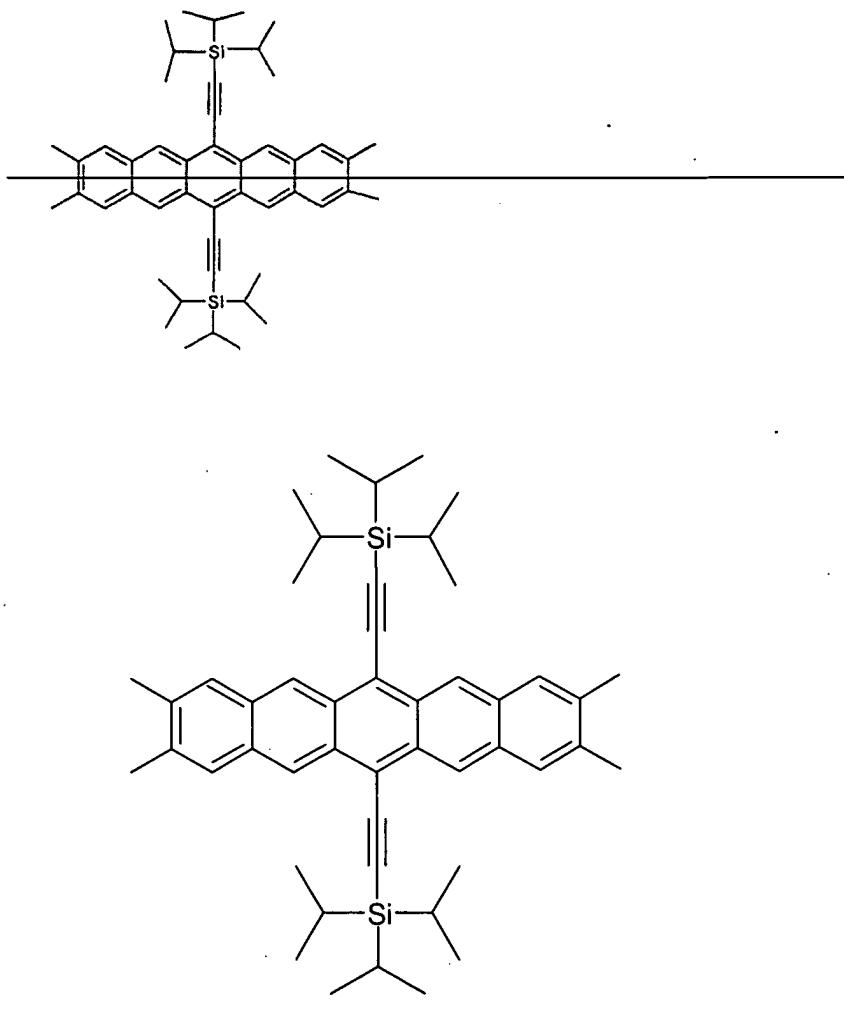


Formula 1

wherein the binder is poly(α -methylstyrene), linear olefin and cycloolefin(norbornene)copolymer, poly(4-methylstyrene), polystyrene or polystyrene-*co*- α -methylstyrene; and the solvent is toluene, ethylcyclohexane, anisole or pxylene.

24. (Currently Amended) An OFET device, comprising an organic semiconducting layer formulation, wherein the organic semiconducting layer formulation comprises:

- a compound of Formula 2;
- a binder; and
- solvent,

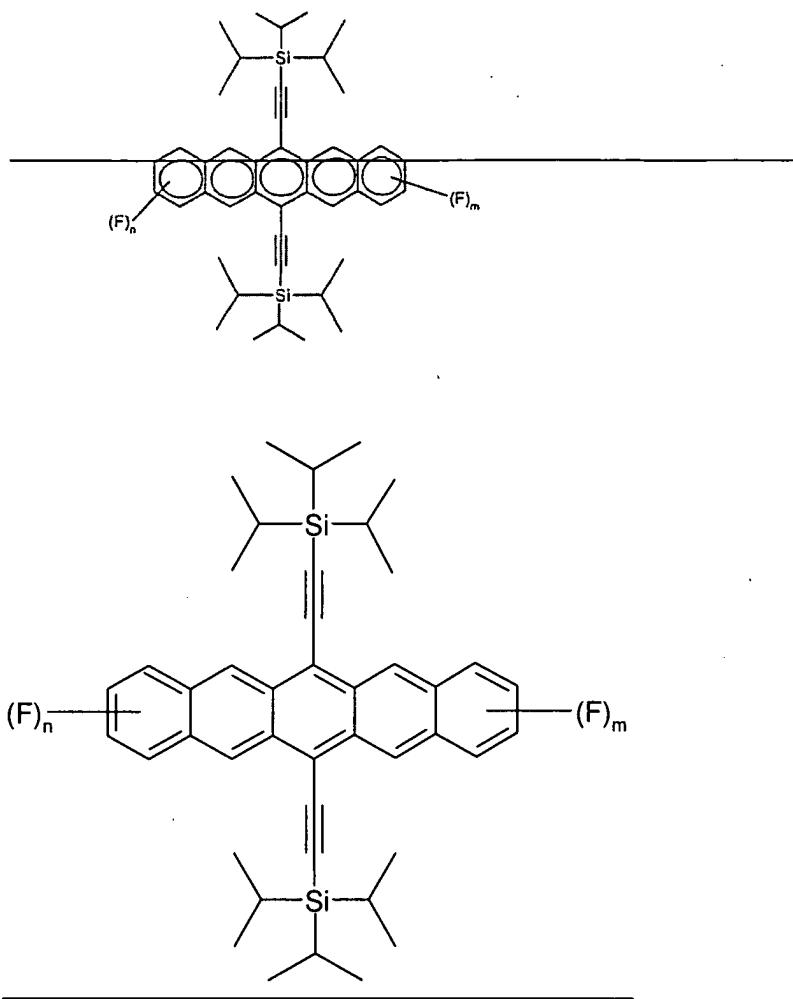


Formula 2

wherein the binder is poly(α -methylstyrene), polyvinylcinnamate, or poly(4-vinylbiphenyl); and the solvent is 1,2-dichlorobenzene.

25. (Currently Amended) An OFET device, comprising an organic semiconducting layer formulation, wherein the organic semiconducting layer comprises:

- a compound of Formula 3;
- a binder; and
- a solvent,

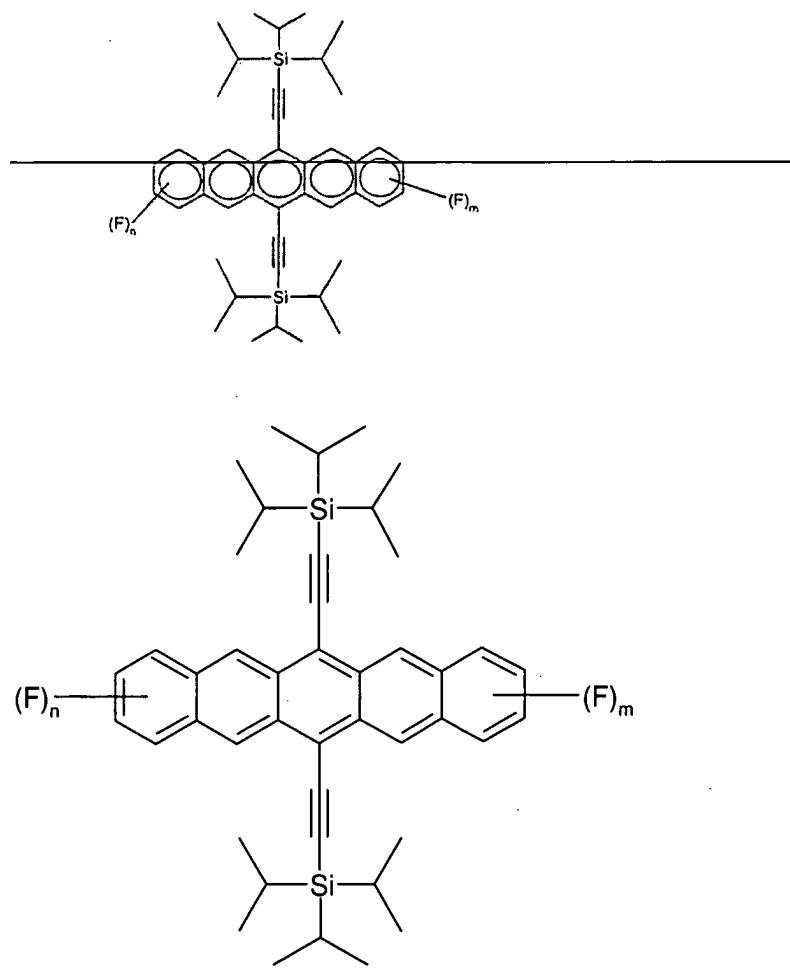


Formula (3)

wherein :

n and m are each independently 0, 1, 2, 3 or 4; the binder is poly(α -methylstyrene); and the solvent is toluene.

26. (Currently Amended) A compound of Formula 3



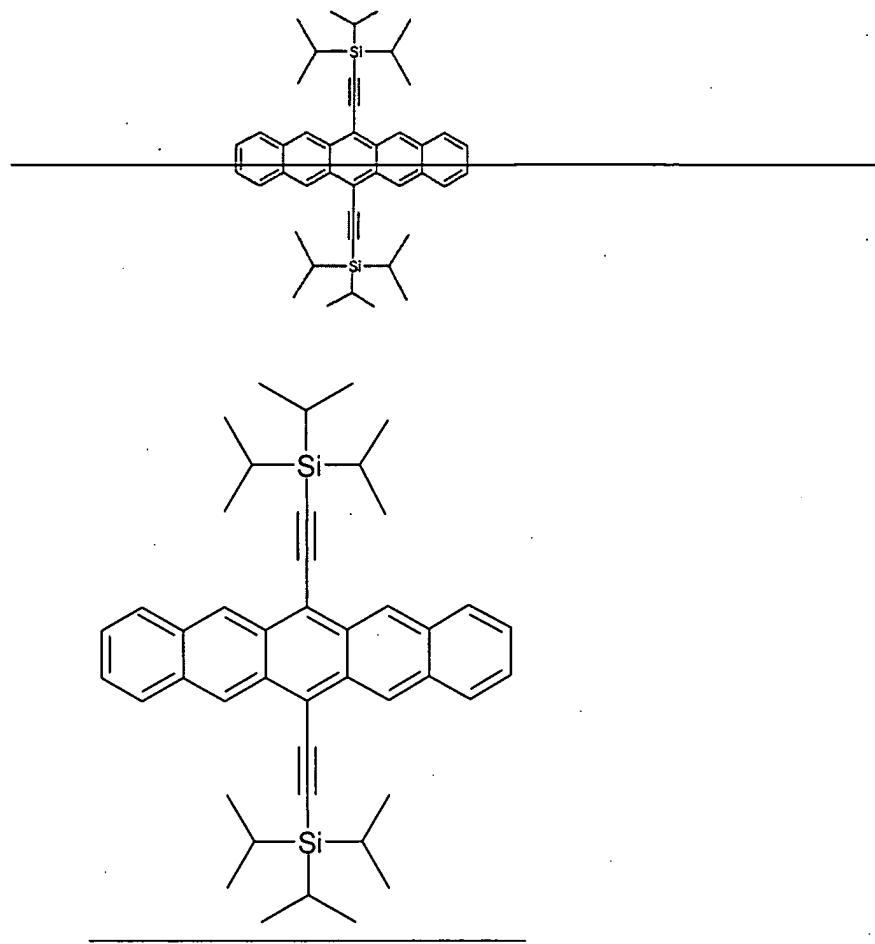
Formula (3)

wherein n and m are each independently 1 or 3.

27. (Previously Presented) An organic semiconducting layer formulation as claimed in claim 1, wherein the halogen group is Cl, Br or F.

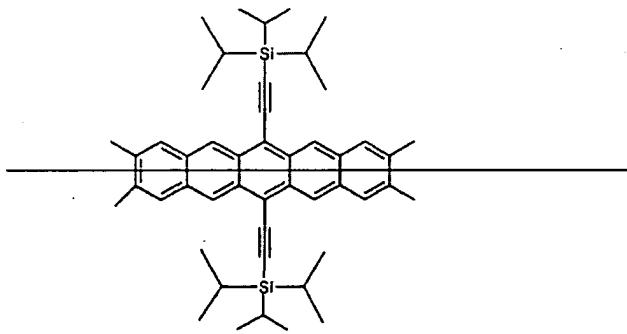
28. (Currently Amended) An organic semiconducting layer formulation, comprising an organic binder which has a permittivity, ϵ , at 1,000 Hz of 3.3 or less; and a polyacene compound which is

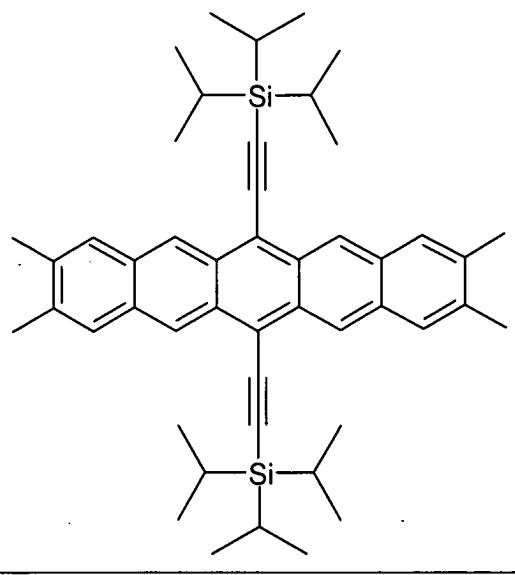
- a) 6, 13-bis(triisopropylsilyl)pentacene of Formula 1,



Formula 1;

b) 2,3,9,10-tetramethyl,6,13-bis (triisopropylsilyl)ethynyl)pentacene of Formula 2:

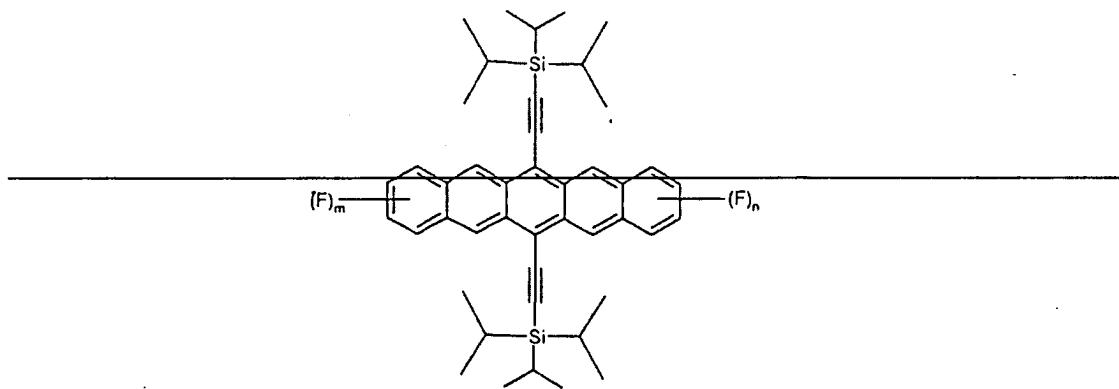


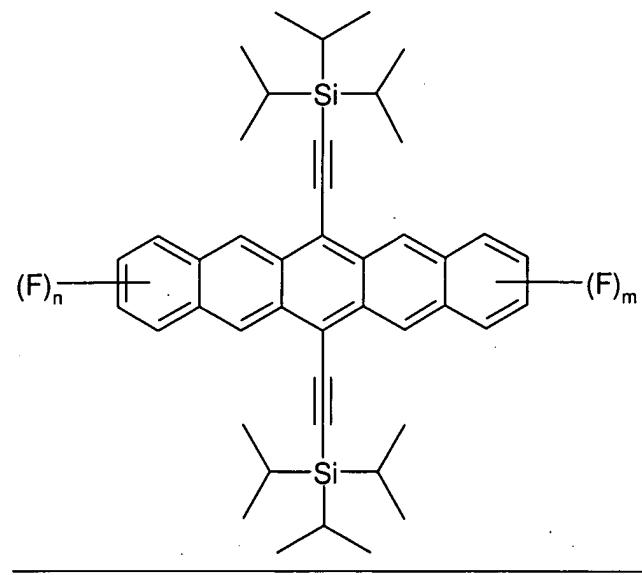


Formula 2;

or

c) of Formula 3:





Formula 3

wherein n and m are each independently 0, 1, 2, 3 or 4.